

L Number	Hits	Search Text	DB	Time stamp
1	2493	((250/306,307,309).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:44
2	6285	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:46
3	0	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and (meaur\$6 near4 (area or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:47
4	19	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:48
5	4	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground)) and (display\$4 near5 bright\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:50
6	1	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground)) and (display\$4 near5 bright\$4)) and ((250/306,307,309).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:50

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5	4	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground) and (display\$4 near5 bright\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:50
6	1	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground) and (display\$4 near5 bright\$4) and ((250/306,307,309).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:52
7	4	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground) and (display\$4 near5 bright\$4) and (map\$4 or chart\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:53
8	4	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground) and (display\$4 near5 bright\$4) and (map\$4 or chart\$4) and ((averag\$4 or accumul\$4) near current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:54
9	4	((inspect\$5 with (hole or semiconductor or wafer or sample)) and (electron or (charged adj particle) or charged-particle)) and ((detect\$4 or measur\$7) near4 current near4 ground) and (display\$4 near5 bright\$4) and (map\$4 or chart\$4) and ((averag\$4 or accumul\$4) near current) and time	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:54